EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	32	(south near epitaxy near corporation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 11:57
L2	0	"10707084"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 11:57
L3	1	"10/707084"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 11:59
L4	3367	high near resistivity near2 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 11:59
L5	3367	high near resistivity near2 (interlaye or inter-layer or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 11:59
L6	3368	high near resistivity near2 (interlayer or inter-layer or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:00
L7	30	high near resistivity near2 (interlayer or inter-layer or layer) near2 GaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:00
L10	193	"Al.sub.xIn.sub.yGa.sub.1-x-yN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:25
L11	209	"Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:28

L12	1	((resistive or resistivity) near10 ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:27
L13	2	((resistive or resistivity or interlayer) near10 ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:27
L14	2	((resistive or resistivity or interlayer or inter-layer) near10 ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:27
L15	2	((resistive or resistivity or interlayer or inter-layer) near10 (("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:27
L16	36	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN") and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 12:28
L17	18	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN") and nucleation and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:43
L18	104	(sheu and lai)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:50
L19	3481	(257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:55
L20	355	l19 and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:51
L21	72	l19 and (leakage near current) and (high near (resistance or resistor or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:52

EAST Search History

L22	22	I19 and (leakage near current) same (high near (resistance or resistor or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:53
L23	2	I19 and (leakage near current) same (high near (resistance or resistor or resistivity) same (nitride or gan or algan or alingan))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:54
L24	5	(257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls.) and ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:55
L25	5	(257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls.) and (("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:56
L26	1	(257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls.) and (("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN")) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:56
L27	30	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN")) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 13:57
L28	3	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN")) same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:16
L29	340	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or AlInGaN or GaN)) same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:17
L30	69	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or AlInGaN or GaN)) near10 layer near10 (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:20

EAST Search History

L31	89	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (indirum near2 aluminum near2 gallium near2 nitride))) near10 layer with (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:20
L32	205	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (indirum near2 aluminum near2 gallium near2 nitride))) near10 layer same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:22
L33	1066	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (indirum near2 aluminum near2 gallium near2 nitride) or ((resistor or resistive or resistivity or resistance) near2 layer))) near10 layer same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:21
L34	1238	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indirum near2 aluminum near2 gallium near2 nitride))) near10 layer same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:22
L35	1238	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride))) near10 layer same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:23
L36	444	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride))) near10 layer near10 (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:22
L37	862412	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:24

EAST Search History

L38	29769	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride))) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:24
L39	47118	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (resistance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride))) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:24
L40	20478	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (resistance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride)) same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:24
L41	352	(("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or AlInGaN or GaN or (resistance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride)) same (leakage near current) and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:26
L42	1814	(electrode same (semiconductor near layer) same (active near layer) and ohmic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:27
L43	996	(electrode same (semiconductor near layer) same (active near layer) same ohmic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:27
L44	74	(electrode same (semiconductor near layer) same (active near layer) same ohmic same ("Al.sub. aIn.sub.bGa.sub.1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:29

EAST Search History

L45	2	(electrode same (semiconductor near layer) same (active near layer) same ohmic same ("Al.sub.aIn.sub.bGa.sub.1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride))) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:29
L46	56	(electrode same (semiconductor near layer) same (active near layer) same ("Al.sub.aIn.sub.bGa.sub.1-a-bN" or AlInGaN or GaN or (ressitance or resistive or resistivity or resistor) or (indium near2 aluminum near2 gallium near2 nitride))) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:33
L47	164	("Al.sub.aIn.sub.bGa.sub.1-a-bN" or AlInGaN or (indium near2 aluminum near2 gallium near2 nitride)) and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:36
L48	0	"Al.sub.xIn.sub.yGa.sub.1-x-yN" near10 leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:35
L49	0	"Al.sub.xIn.sub.yGa.sub.1-x-yN" with leakage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:35
L50	193	"Al.sub.xIn.sub.yGa.sub.1-x-yN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:36
L51	3	"Al.sub.xIn.sub.yGa.sub.1-x-yN" same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:38
L52	3	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN") same (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:59

L53	30	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN") and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:39
L54	6	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN") and (leakage near current) and nucleation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:39
L55	0	l52 and (strangulation same (dope or doped or doping))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 14:59
L56	357743	((highly or high) near2 (resistivity or resistance or resistor or resistive))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:04
L57	1867	((highly or high) near2 (resistivity or resistance or resistor or resistive)) with (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:04
L58	0	((highly or high) near2 (resistivity or resistance or resistor or resistive)) with (leakage near current) with "Al.sub.xIn.sub.yGa.sub.1-x-yN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:05
L59	0	((highly or high) near2 (resistivity or resistance or resistor or resistive)) with (leakage near current) same "Al.sub.xIn.sub.yGa.sub.1-x-yN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:05
L60	0	((highly or high) near2 (resistivity or resistance or resistor or resistive)) same (leakage near current) same "Al.sub.xIn.sub.yGa.sub.1-x-yN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:05
L61	0	(((highly or high) near2 (resistivity or resistance or resistor or resistive)) or high-resistivity) same (leakage near current) same "Al.sub.xIn.sub.yGa.sub.1-x-yN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:05
L62	5	(((highly or high) near2 (resistivity or resistance or resistor or resistive)) or high-resistivity) same "Al.sub.xIn.sub.yGa.sub.1-x-yN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:06

EAST Search History

L63	209	"Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:07
L64	30	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN") and (leakage near current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:59
L65	1	I64 and ((current near2 strangulation) near10 (implant or implanting or implanted or implantation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:52
L66	40	(US-20040080010-$ or US-20030062525-$ or US-20030015708-$ or US-20030146444-$ or US-20050012113-$ or US-20020074553-$ or US-20030218183-$ or US-20060199289-$ or US-20060226417-$ or US-20030122147-$ or US-20020096687-$ or US-20030127658-$ or US-20030214807-$ or US-20050082543-$ or US-20050167680-$ or US-20050274964-$ or US-20030071276-$ or US-20030047744-$ or US-20050167697-$).did. or (US-6586272-$ or US-5677538-$ or US-5598014-$ or US-6455340-$ or US-5847397-$ or US-6495852-$ or US-6429467-$ or US-5977565-$ or US-5932905-$ or US-5717235-$ or US-5707887-$ or US-5507881-$ or US-6208074-$ or US-5673220-$ or US-7151281-$).did. or (JP-06216404-$).did. or (US-20030230235-$ or US-20050032345-$ or JP-06216404-$ or US-20050012113-$ or EP-296371-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/04/23 15:58

L67	71	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN") same (active near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 15:59
L68	73	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or "Al.sub.eIn.sub.fGa. sub.1-e-fN") same (active near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:00
L69	35	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or "Al.sub.eIn.sub.fGa. sub.1-e-fN") near10 (active near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:00
L70	69	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or "Al.sub.eIn.sub.fGa. sub.1-e-fN") near10 ((semiconductor or active) near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:06
L71	1	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or "Al.sub.eIn.sub.fGa. sub.1-e-fN") near10 ((semiconductor or active) near layer) and (electrode near10 (finger or interlaced))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:04
L72	1	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or "Al.sub.eIn.sub.fGa. sub.1-e-fN") near10 ((semiconductor or active) near layer) and ((finger-shaped or finger or interlaced))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:04
L73	26	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or "Al.sub.eIn.sub.fGa. sub.1-e-fN") near10 ((semiconductor or active) near layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:04
L74	8	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub. 1-a-bN" or "Al.sub.eIn.sub.fGa. sub.1-e-fN") near10 ((semiconductor or active) near layer) and ("Al.sub.xIn.sub.yGa. sub.1-x-yN" or "Al.sub.aIn.sub. bGa.sub.1-a-bN" or "Al.sub.eIn. sub.fGa.sub.1-e-fN") near10 ((nucleation or buffer) near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:08

L75	4	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN") near10 ((semiconductor or active) near layer) and ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN") near10 ((nucleation or buffer) near layer) and ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN") near10 ((clad or contact) near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:08
L76	4	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN") near10 ((semiconductor or active) near layer) and ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN") near10 ((nucleation or buffer) near layer) and ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN") near10 ((cladding or clad or contact) near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:09
L77	5	("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN" or "Al.sub.cIn.sub.dGa.sub.1-c-dN") near10 ((semiconductor or active) near layer) and ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN" or "Al.sub.cIn.sub.dGa.sub.1-c-dN") near10 ((nucleation or buffer) near layer) and ("Al.sub.xIn.sub.yGa.sub.1-x-yN" or "Al.sub.aIn.sub.bGa.sub.1-a-bN" or "Al.sub.eIn.sub.fGa.sub.1-e-fN" or "Al.sub.cIn.sub.dGa.sub.1-c-dN") near10 ((cladding or clad or contact) near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:10

L78	41	(US-20040080010-$ or US-20030062525-$ or US-20030015708-$ or US-20030146444-$ or US-20050012113-$ or US-20020074553-$ or US-20030218183-$ or US-20060199289-$ or US-20060226417-$ or US-20030122147-$ or US-20020096687-$ or US-20030127658-$ or US-20030214807-$ or US-20050082543-$ or US-20050167680-$ or US-20050274964-$ or US-20030071276-$ or US-20030047744-$ or US-20050167697-$ or US-20040124435-$).did. or (US-6586272-$ or US-5677538-$ or US-5598014-$ or US-6455340-$ or US-5847397-$ or US-6495852-$ or US-6429467-$ or US-5977565-$ or US-5932905-$ or US-5717235-$ or US-5707887-$ or US-5507881-$ or US-6208074-$ or US-5673220-$ or US-7151281-$).did. or (JP-06216404-$).did. or (US-20030230235-$ or US-20050032345-$ or JP-06216404-$ or US-20050012113-$ or EP-296371-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/04/23 16:25
L79	4	l78 and (electrode near10 (finger or finger-shaped or interlaced))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:28
L80	4	l78 and (electrode near10 (finger or finger-shaped or interlaced) or interdigitated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:28
L81	25234	(electrode near10 (finger or finger-shaped or interlaced) or interdigitated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:28

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L82	192	((nucleation or buffer) near layer) and ((active or semicondcutor) near layer) and (electrode near10 (finger or finger-shaped or interlaced) or interdigitated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:29
L83	134	((nucleation or buffer) near layer) and ((active or semicondcutor) near layer) and ((contact or clad or cladding) near layer) and (electrode near10 (finger or finger-shaped or interlaced) or interdigitated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:30
L84	77	((nucleation or buffer) near layer) and ((active or semicondcutor) near layer) and ((contact or clad or cladding) near layer) and (electrode near10 (finger or finger-shaped or interlaced) or interdigitated) and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:30
L85	78	((nucleation or buffer) near layer) and ((active or semicondcutor) near layer) and ((contact or clad or cladding) near layer) and (electrode near10 (finger or finger-shaped or interlaced) or interdigitated) and (nitride or GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 16:30